EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	525119	(opening groove via recess depress$3 trench hole) with (etch etching etch$3 pattern patterning pattern$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/10 13:09
S2	127055	(opening groove via recess depress$3 trench hole) with (etch etching etch$3 pattern patterning pattern$3) with (insulating insulation insulat$3 interlayer dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/10 13:11
S3	140675	(opening groove via recess depress$3 trench hole) with (etch etching etch$3 pattern patterning pattern$3) with (mask masking mask$3 hardmask$3 phoresist photoresist resist$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/10 13:12
S4	1	10/593386	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 18:18
S6	182	"4,214,918" "4,583,011" "4,766,516" "4,920,402" "5,336,624" "5,468,990" "5,783,846" "5,821,582" "5,824,571"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:33

S7	117	"5,866,933" "5,883,000" "5,930,663" "5,973,375" "6,064,110" "6,117,762" "6,294,816" "6,360,321" "6,496,119" "6,515,304" "6,613,661" "6,720,656"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:33
S8	6	"20010033012" "20020173131"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:34
S9	250	S6 S7 S8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:35
S10	148	S9 and (interconnecting interconnection interconnect$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:36
S11	139	S10 and (die chip "IC" integrated adj circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:37
S12	68	S11 and (annealing annealed anneal$3 heat heating thermal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 08:38
S13	9	("4088799" | "4843034" | "4906591" | "5087589" | "5232863" | "5317197" | "5726805" | "5883000" | "6262486").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/24 09:14

S14	6	("4088799" | "4906591" | "5232863" | "5317197" | "5726805" | "5883000").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/24 09:15
S15	6	("4088799" | "4906591" | "5232863" | "5317197" | "5726805" | "5883000").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/24 09:15
S16	9345	(direct near3 writing writ$3) with (interconnecting interconnection interconnect$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:16
S17	27	(direct near3 writing writ$3) with (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:17
S18	6	(direct near3 writing writ$3) with (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (anneal$3 heat$3 thermal$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:17
S19	6	(direct near3 writing writ$3) with (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (anneal$3 heat$3 thermal$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:18
S20	27	(direct near3 writing writ$3) with (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:18

S21	3	(direct near3 (writing writ$3)) with (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:19
S22	712	(interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (conductor conductive near3 path)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:23
S23	529	S22 and (die chip "IC" integrated adj circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:23
S24	453	S22 and (annealing annealed anneal$3 heat heating thermal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:23
S25	80	S24 and shield$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:26
S26	60	S22 and (annealing annealed anneal$3 heat heating thermal) near4 (beam laser irradiat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:51
S27	712	(interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (conductor conductive near3 path)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:51
S28	60	S22 and (annealing annealed anneal$3 heat heating thermal) near4 (beam laser irradiat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:51

S29	27284	doped near3 (circuit path conductive conducting)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 11:49
S30	712	S22 and (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (conductor conductive near3 path)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 11:49
S31	164	S29 and (interconnecting interconnection interconnect$4) with (implant$4 doped doping dopant) with (conductor conductive near3 path)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 11:50

2/24/2009 5:18:08 PM
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